

100

Fig. 1A

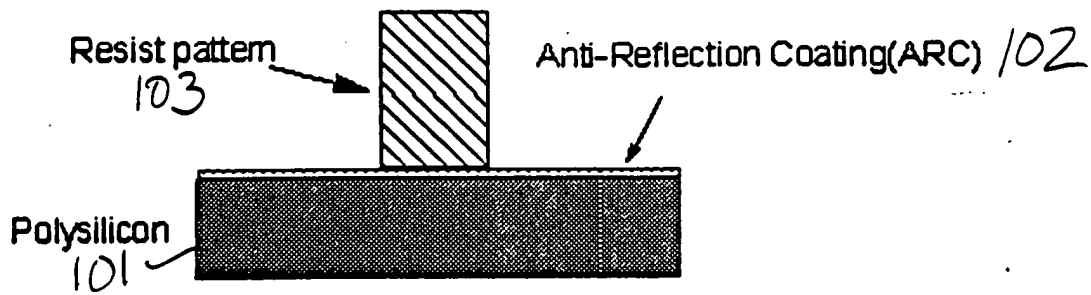
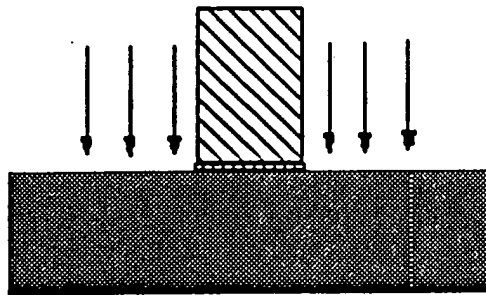


Fig. 1B



ARC etch

Fig. 1C

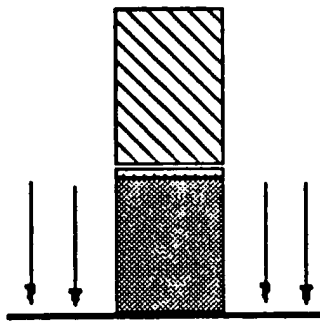
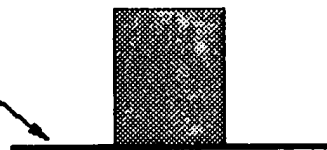
polysilicon etch
(gate RIE)

Fig. 1D

gate oxide 104



Strip resist/ARC

200

Fig. 2A

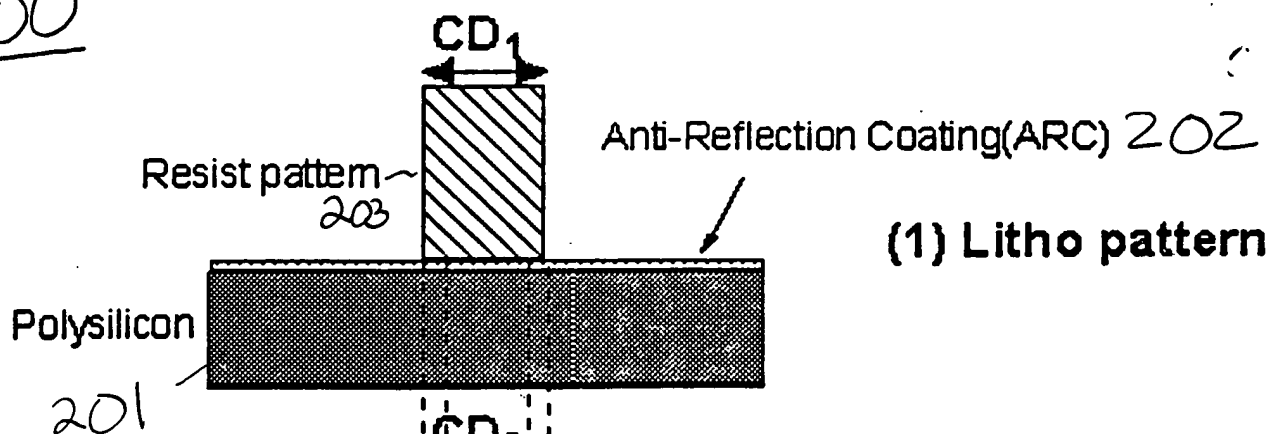
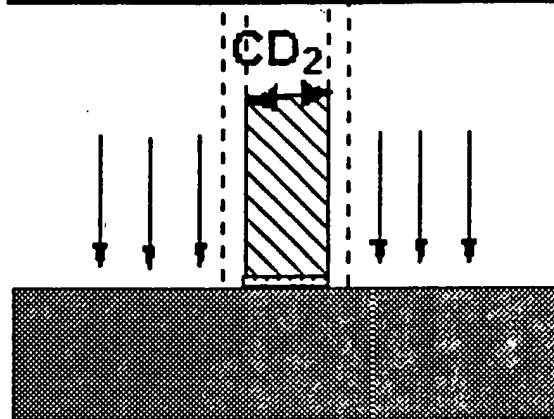


Fig. 2B



$$CD_2 < CD_1$$

	Litho tool	Line-width resist	O ₂ trim time	Line-width after trim	Line-width poly	Leff
6X	MSII	0.20	20s	0.18	0.18	0.15
8S	MSIII	0.15	20s	0.13	0.13	0.09
8S2					0.10	0.07

Fig. 2C

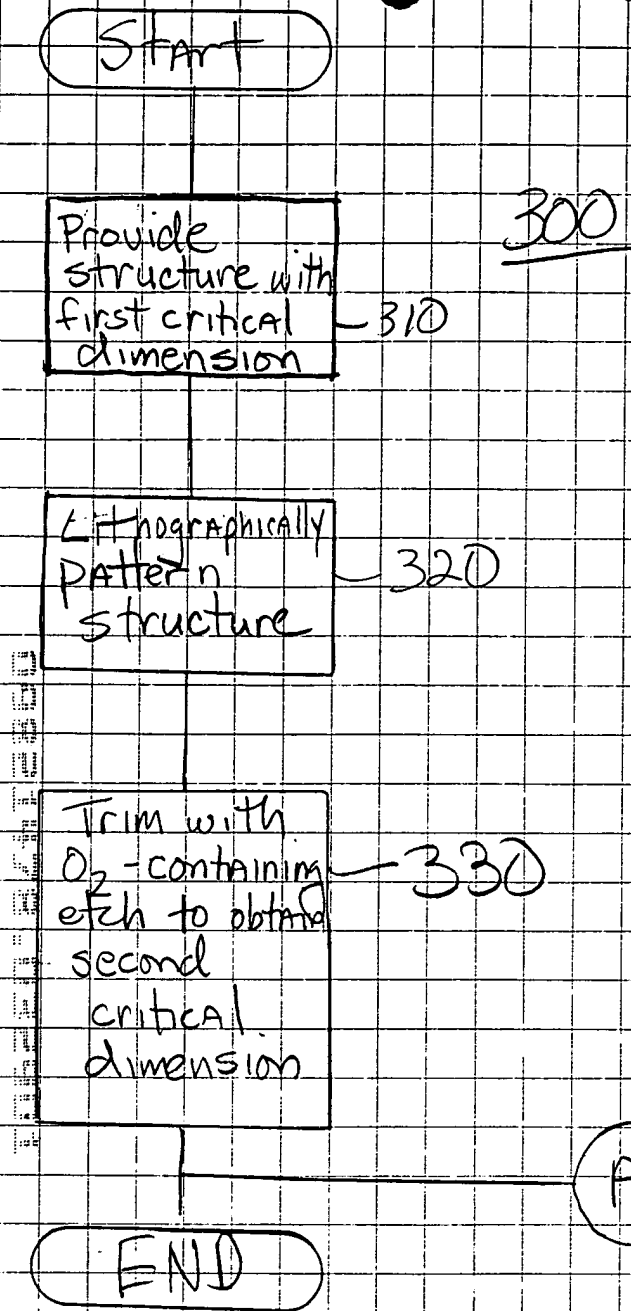


Figure 3

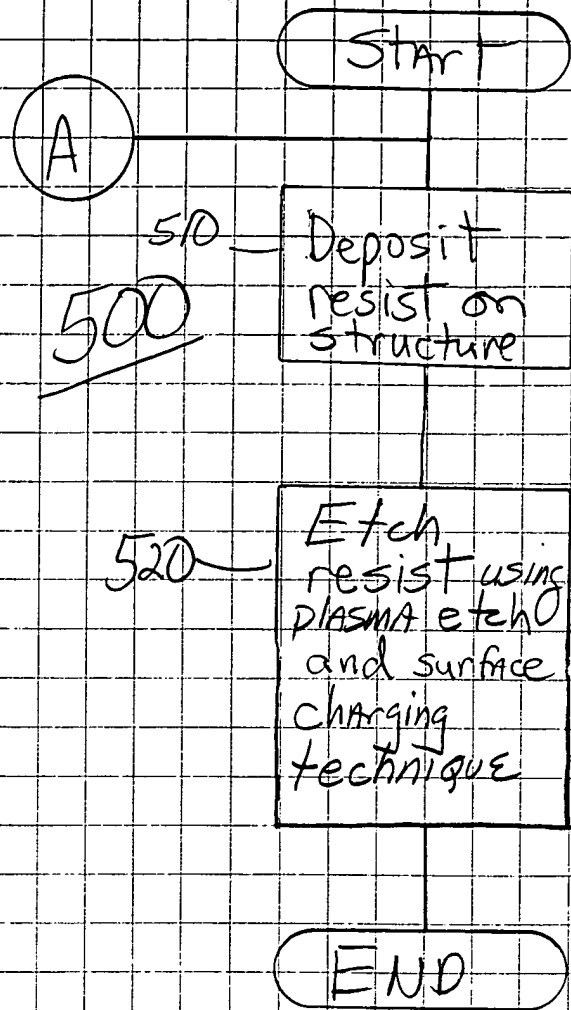


Figure 5

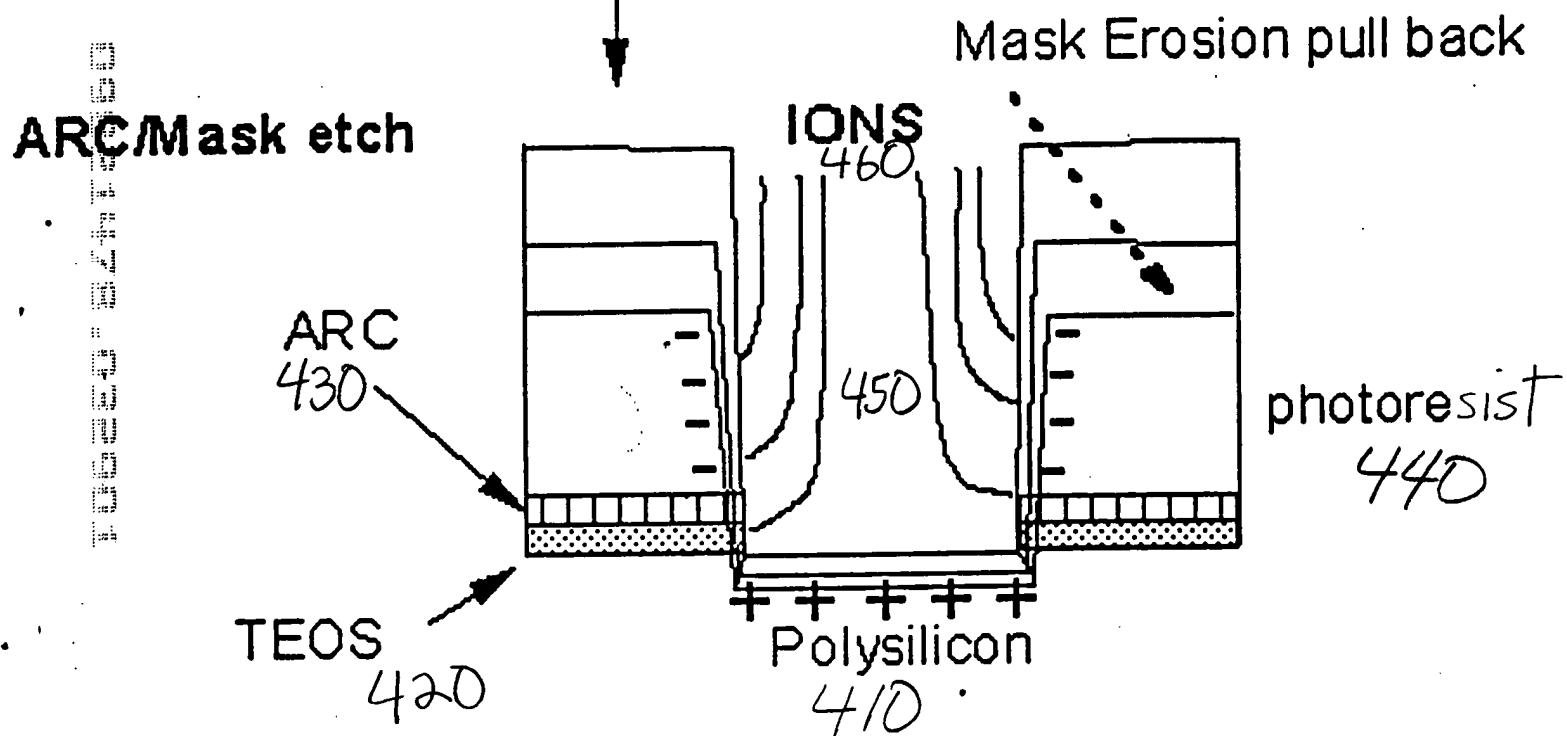
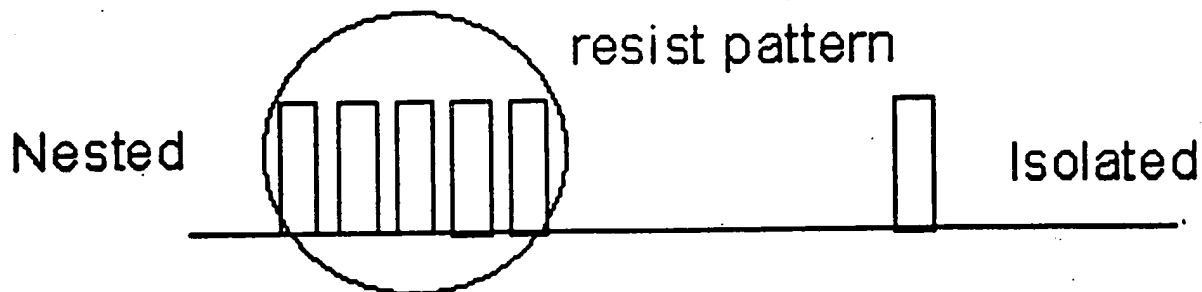
400

Figure 4